

**BC556, B
BC557, A, B, C
BC558, B** TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.625 W ($T_{amb}=25^{\circ}C$)

Collector current

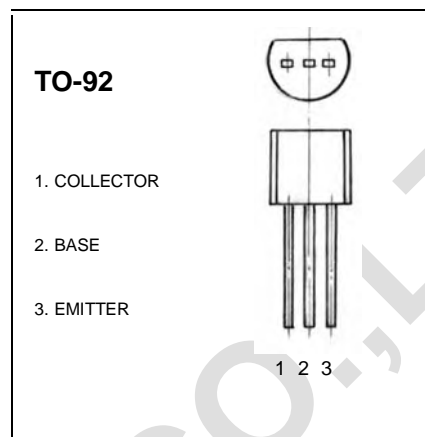
I_{CM} : -0.1 A

Collector-base voltage

V_{CBO} : BC556 -80 V
BC557 -50 V
BC558 -30 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	BC556 BC557 BC558	V_{CBO} $I_C = -100\mu A, I_E = 0$	-80 -50 -30		V
Collector-emitter breakdown voltage	BC556 BC557 BC558	V_{CEO} $I_C = -2mA, I_B = 0$	-65 -45 -30		V
Emitter-base breakdown voltage	BC556 BC557 BC558	V_{EBO} $I_E = -100\mu A, I_C = 0$	-6		V
Collector cut-off current	BC556 BC557 BC558	I_{CBO} $V_{CB} = -70V, I_E = 0$ $V_{CB} = -45V, I_E = 0$ $V_{CB} = -25V, I_E = 0$		-0.1	μA
Collector cut-off current	BC556 BC557 BC558	I_{CEO} $V_{CE} = -60V, I_B = 0$ $V_{CE} = -40V, I_B = 0$ $V_{CE} = -25V, I_B = 0$		-0.1	μA
Emitter cut-off current	BC556 BC557 BC558	I_{EBO} $V_{EB} = -5V, I_C = 0$		-0.1	μA
DC current gain	BC556 BC557 BC558 BC557A BC556B/BC557B/BC558B BC557C	$h_{FE(1)}$ $V_{CE} = -5V, I_C = -2mA$	120 120 120 120 180 420	500 800 800 220 460 800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -5mA$		-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100mA, I_B = -5mA$		-1	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$ $f = 100MHz$	150		MHz